

### IN THE SPECIFICATION

Please replace paragraph 0035 with the following new paragraph:

~~Substrate 801 also has an ILD layer 806 deposited thereon. ILD layer 806 has a trench formed therein that contains FPF 808, a diffusion barrier layer 809. Metal layer 810 forms the top electrode of a FPMD. Structure 800 has other FPMDs, shown for example as vias 813a, 813b, and 813c. For one embodiment, the trenches and vias of structure 800 are formed using a trench first dual damascene process. Alternatively, a typical prior art process consisting of etching a via and sputtering metal may be used to form the vias of structure 800. In accordance with various alternative embodiments of the invention a trench first dual damascene process may be used to form trenches and vias to connect conventionally produced FPMDs of the prior art.~~

Substrate 801 also has an ILD layer 806 deposited thereon. ILD layer 806 has a trench formed therein that contains FPF 808, a diffusion barrier layer 809. Metal layer 810 forms the top electrode of a FPMD. Metal layer 810 is capped with a diffusion barrier layer 811. Structure 800 has other FPMDs, shown for example as vias 813a, 813b, and 813c. For one embodiment, the trenches and vias of structure 800 are formed using a trench-first dual damascene process. Alternatively, a typical prior art process consisting of etching a via and sputtering metal may be used to form the vias of structure 800. In accordance with various alternative embodiments of the invention a trench-first dual damascene process may be used to form trenches and vias to connect conventionally produced FPMDs of the prior art.